

**FEATURES**

- TO-8 Hermetic Package
- Optimized Die Size for Maximum Signal
- Low Capacitance

**Electro-Optical Characteristics at 25°C**

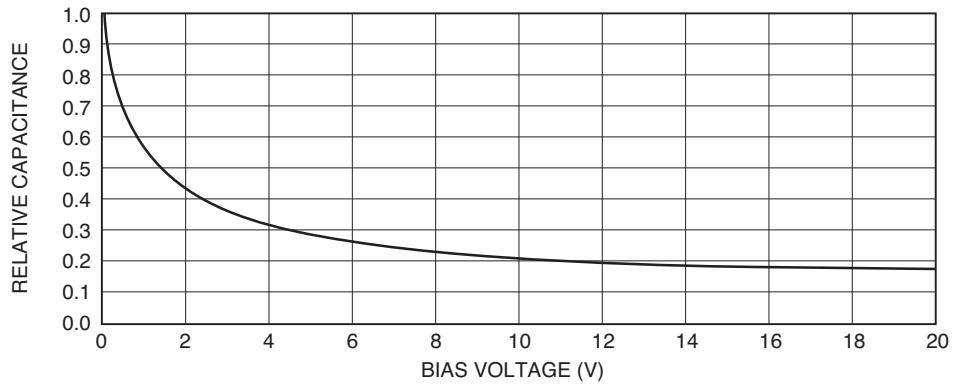
Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	9.91 mm x 4.28 mm		42		mm <sup>2</sup>
Responsivity	@ 450 nm	0.2	0.28		A/W
Dark Current, I <sub>dr</sub>	V <sub>R</sub> = 10 V		11	25	nA
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 10 μA	25	60		Volts
Capacitance, C	V <sub>R</sub> = 10 V		85		pF
Rise Time	V <sub>R</sub> = 10 V		30		nsec
Series Resistance	V <sub>f</sub> = 1 V		35	100	Ohms

**Thermal Parameters**

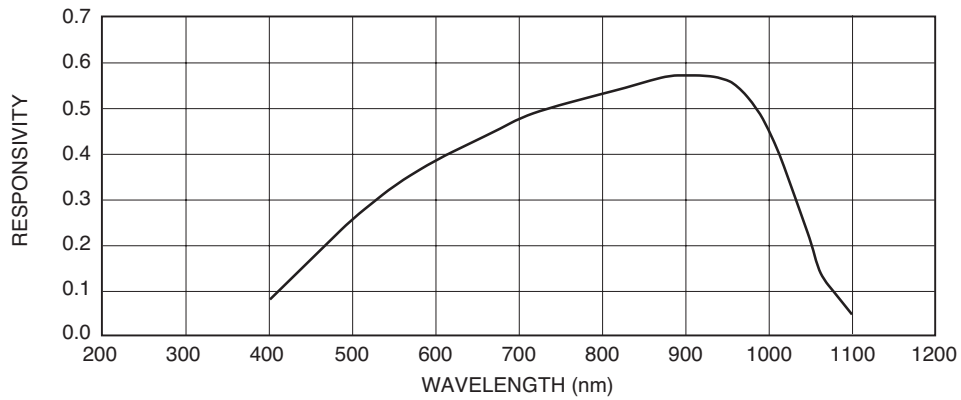
Parameters	Units
Storage and Operating Temperature Range	-55°C to 100°C
Maximum Junction Temperature	100°C
Lead Soldering Temperature <sup>1</sup>	260°C

<sup>1</sup> 1/16" from case for 10 seconds.

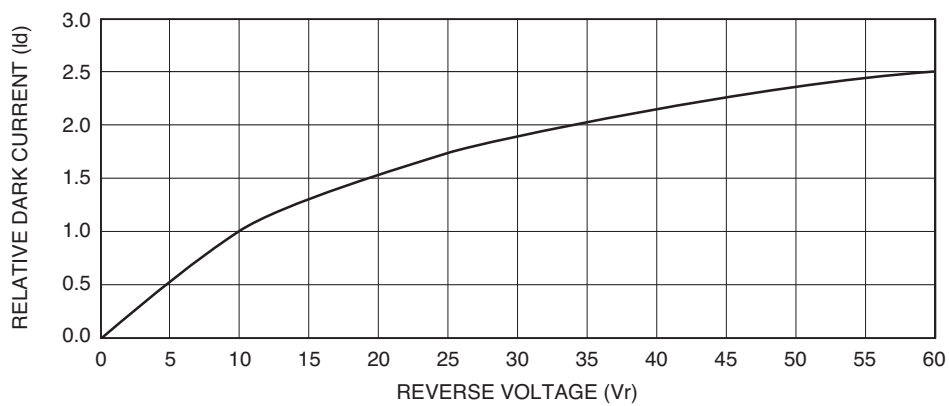
Capacitance vs Bias Voltage



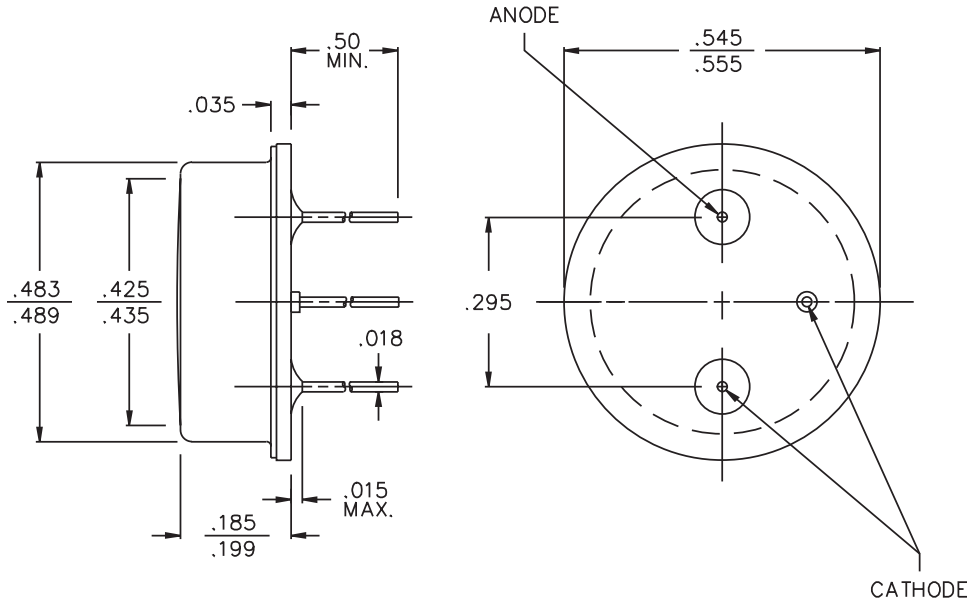
Typical Spectral Response



Dark Current vs Voltage



**Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.